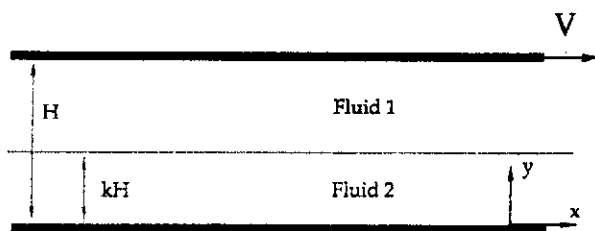


本試題是否可以使用計算機: 可使用, 不可使用 (請命題老師勾選)

- (8%) 一顆直徑為 D_1 、密度為 ρ_s 的圓球在密度為 ρ_1 、黏度為 μ_1 的流體中沉降, 其終端速度 (terminal velocity) 為 v_{∞} 。另有一顆材質相同, 但直徑為 D_2 ($D_2 = 2D_1$) 的圓球在相同密度 ($\rho_2 = \rho_1$)、但黏度為 μ_2 ($\mu_2 = 3\mu_1$) 的流體中沉降, 請問這顆球的終端速度為多少? 假設兩者流場皆為 creeping flow, 其 drag coefficient $C_D = 24/Re$ 。請詳細寫出計算過程。
- (12%) 如下圖所示, 下層板固定, 兩不互溶的牛頓流體在平行平板間的流動是由於上層板以 V 的恒定速度往右拉動所造成的。假設流體的密度與黏度都為常數, 分別為 ρ_1 、 ρ_2 與 μ_1 、 μ_2 , steady state, 不考慮 end effects, $v_y = v_z = 0$, $v_x = v_x(y)$ only。假設 $\mu_1 = 3\mu_2$, $k = 1/3$, 求流體的速度分佈。



The Navier-Stokes equations for constant ρ and μ in Cartesian coordinates are:

x direction

$$\rho \left(\frac{\partial v_x}{\partial t} + v_x \frac{\partial v_x}{\partial x} + v_y \frac{\partial v_x}{\partial y} + v_z \frac{\partial v_x}{\partial z} \right) = -\frac{\partial P}{\partial x} + \rho g_x + \mu \left(\frac{\partial^2 v_x}{\partial x^2} + \frac{\partial^2 v_x}{\partial y^2} + \frac{\partial^2 v_x}{\partial z^2} \right)$$

y direction

$$\rho \left(\frac{\partial v_y}{\partial t} + v_x \frac{\partial v_y}{\partial x} + v_y \frac{\partial v_y}{\partial y} + v_z \frac{\partial v_y}{\partial z} \right) = -\frac{\partial P}{\partial y} + \rho g_y + \mu \left(\frac{\partial^2 v_y}{\partial x^2} + \frac{\partial^2 v_y}{\partial y^2} + \frac{\partial^2 v_y}{\partial z^2} \right)$$

3.

Energy exchange between Fluid A and B in a cocurrent flow, single-pass, double-pipe heat exchanger:

Fluid A: mass flow rate=1.0 kg/s, specific heat=1500 J/kg.K, $T_{in}=375$ K

Fluid B: mass flow rate=0.3 kg/s, specific heat=2500 J/kg.K, $T_{in}=280$ K

Overall heat transfer coefficient=225 W/m².K and heat transfer area=5 m²

a. What is the number of heat transfer unit (NTU)? (2%)

b. If using the same heat exchanger but with energy exchange between Fluid A and B in a COUNTERCURRENT flow fashion (same T_{in} as the above), will the NTU(countercurrent) > or = or < NTU(cocurrent)? Explain your answer. (1%)

c. Derive the expression of heat-exchanger effectiveness, ϵ , for the cocurrent flow, single-pass, double-pipe heat exchanger. (5%) What is the value of ϵ for this case? (2%) Evaluate the heat transfer rate, the T_{out} for Fluid A and B, and the logarithmic-mean temperature difference. (4%)

d. Will the effectiveness, ϵ (cocurrent) > or = or < ϵ (countercurrent)? Explain your answer. (2%)

e. For the shell-and-tube heat exchanger, what does it mean by "2-4"? (1%) If we use the shell-and-tube heat exchanger (at the same conditions as described), will the effectiveness, ϵ (shell and tube) > or = or < ϵ (countercurrent)? Explain your answer. (3%)

(背面仍有題目, 請繼續作答)

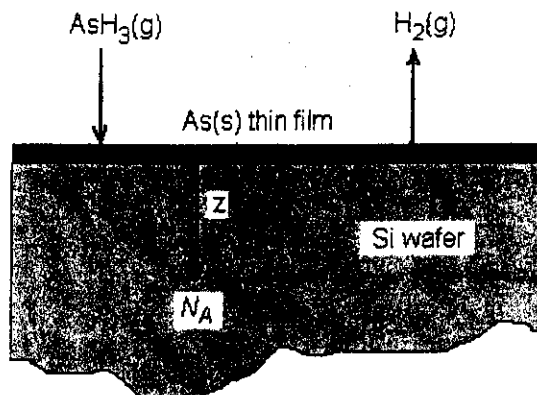
本試題是否可以使用計算機： 可使用， 不可使用（請命題老師勾選）

4.

In the manufacture of semiconducting thin films, a thin film of solid arsenic (As) is laid down onto the surface of a silicon wafer by the chemical vapor deposition of arsine, AsH_3



The arsenic atoms then diffuse into the solid silicon to dope the wafer, as shown in the figure below.



- (a) Write down the simplified governing equation and the appropriate initial and boundary conditions for this problem. (4%)
- (b) Show that the solution can be expressed as

$$\frac{c_{As} - c_A}{c_{As} - c_{A0}} = \text{erf}\left(\frac{z}{2\sqrt{D_{AB}t}}\right)$$

where c_{A0} is the initial concentration of arsenic in the silicon wafer, c_{As} is the surface concentration of arsenic in silicon, and D_{AB} is the diffusivity. (4%) From this result, deduce a relation between the characteristic length of diffusion and $D_{AB}t$. (2%)

- (c) What is the flux of arsenic atoms into the silicon wafer after 30 minutes, in units of atoms/cm²·s? (6%) What is the arsenic concentration one micron into the silicon wafer after one hour, in units of atoms/cm³? (4%) The initial concentration of residual arsenic in the silicon wafer is 10^{12} atoms/cm³. The process temperature is 1050°C. The average diffusivity of arsenic in silicon is 5×10^{-13} cm²/s at this temperature, and the maximum solubility of arsenic in silicon is 2×10^{21} atoms/cm³. The error function can be approximated by

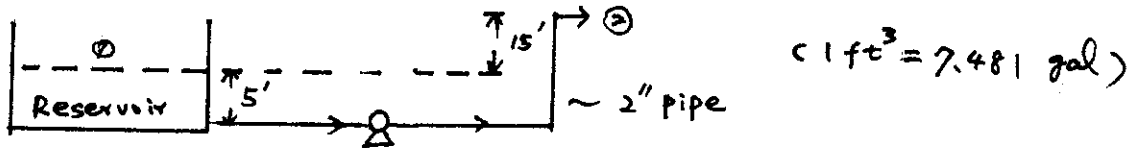
$$\text{erf}(\phi) = 1 - \frac{1}{\sqrt{\pi}} e^{-\phi^2} \quad \text{if } \phi \geq 1 \quad ; \quad \text{erf}(\phi) = \frac{2}{\sqrt{\pi}} \left(\phi - \frac{\phi^3}{3} \right) \quad \text{if } \phi \leq 0.5$$

5. 60 gal/min of a liquid (sp. gr. = 0.85, vapor pressure = 7.2 lbf/in²) is pumped from an open reservoir to a height of 15 feet, as shown in the figure. The frictional pressure losses in the inlet and outlet pipes of the pump are 0.8 lbf/in² and 7.5 lbf/in², respectively. The liquid pressure at point 2 is 45 lbf/in² gauge.

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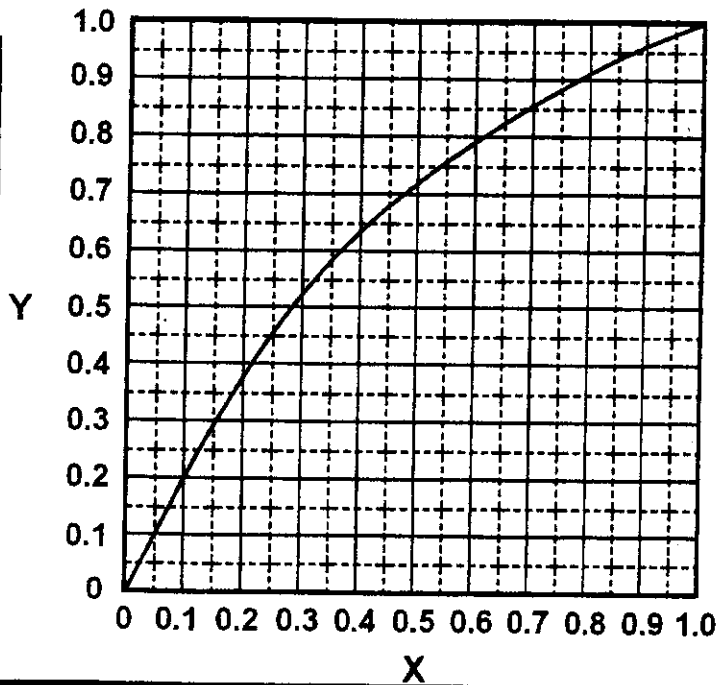
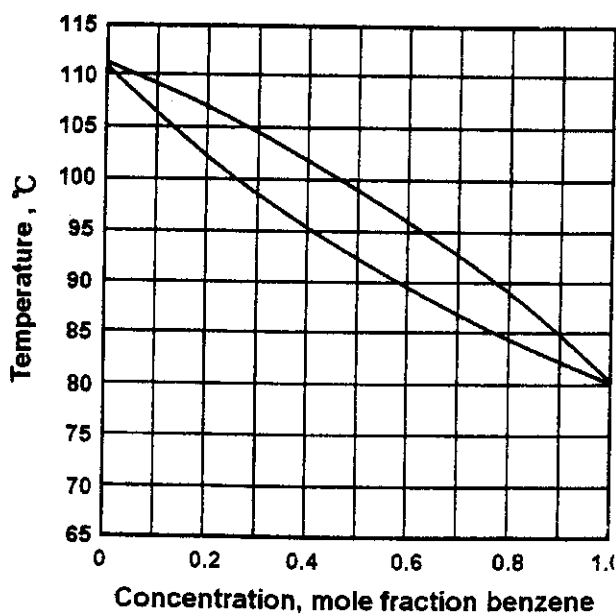
If the pump efficiency is 0.65, determine

- (1) the head developed by the pump (expressed as lb_f/in^2) (15%)
- (2) $NPSH = ?$ (expressed as ft) ($\rho_{\text{H}_2\text{O}} = 62.4 \text{ lb}_m/\text{ft}^3$) (5%)



6.

利用一急驟蒸餾塔 (flash distillation) 分離含 40 mole% benzene in 60 mole% toluene 的混合液體, 混合液先於高壓下加熱至 T_0 , 而後噴入一壓力為 1 atm 的分離塔中。請利用所附的平衡關係圖回答下列問題: (1) 利用此一裝置, 氣相中 Benzene 可被濃縮的最大值 (y_{max}), 及液相中 Benzene 殘餘濃度的最低值 (x_{min}) 為何? (請說明你的作法) (5%); (2) 若進料溶液經分離後, 40% 成為氣相。請求出此一操作條件下分離塔的溫度 (T_f), Benzene 在氣相中的濃度 (y), 及在液相中的濃度 (x)。 (7%); (3) 若要達到上一小題的分離結果, 進料液體的預熱溫度 (T_0) 為何? (8%) (可利用所附方格紙做圖求解, 但必須在答案卷中繪一簡圖說明求解方法)



component	Enthalpy of vaporization, cal/g mol.	Specific heat at constant pressure, cal/g mol. °C		Boiling point, °C
		liquid	Vapor	
Benzene	7360	33	23	80.1
Toluene	7960	40	33	110.6